

ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

MITSUBISHI RF POWER MOS FET

RD07MVS1

Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

DESCRIPTION

RD07MVS1 is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications.

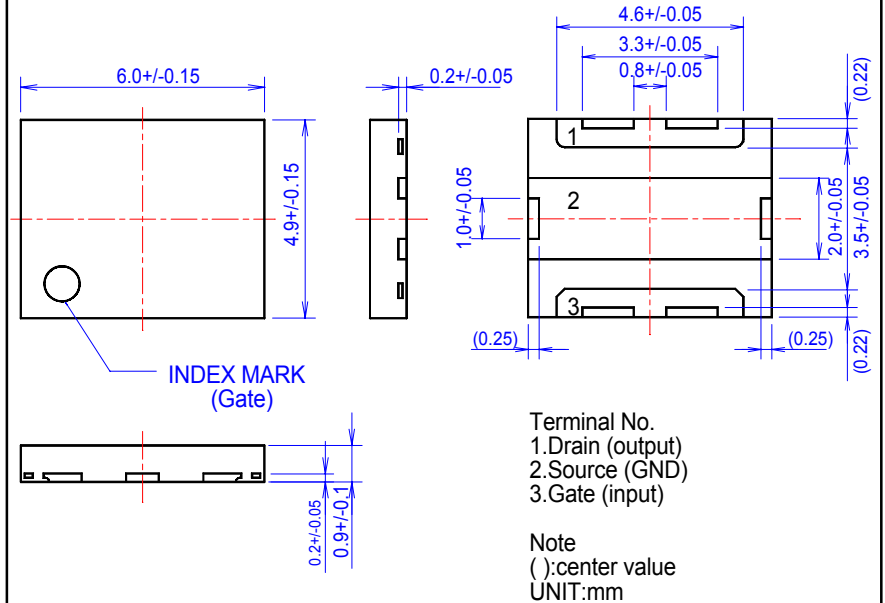
FEATURES

- High power gain:
Pout>7W, Gp>10dB@Vdd=7.2V, f=520MHz
- High Efficiency: 60%typ. (175MHz)
- High Efficiency: 55%typ. (520MHz)

APPLICATION

For output stage of high power amplifiers in VHF/UHF band mobile radio sets.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

(Tc=25°C UNLESS OTHERWISE NOTED)

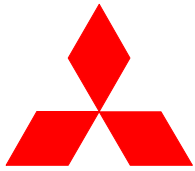
SYMBOL	PARAMETER	CONDITIONS	RATINGS	UNIT
VDSS	Drain to source voltage	Vgs=0V	30	V
VGSS	Gate to source voltage	Vds=0V	+/- 20	V
Pch	Channel dissipation	Tc=25°C	50	W
Pin	Input Power	Zg=Zl=50Ω	1.5	W
ID	Drain Current	-	3	A
Tch	Junction Temperature	-	150	°C
Tstg	Storage temperature	-	-40 to +125	°C
Rth j-c	Thermal resistance	Junction to case	2.5	°C/W

Note 1: Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX.	
IDSS	Zero gate voltage drain current	VDS=17V, VGS=0V	-	-	200	μA
IGSS	Gate to source leak current	VGS=10V, VDS=0V	-	-	1	μA
VTH	Gate threshold Voltage	VDS=12V, IDS=1mA	1.4	1.7	2.4	V
Pout1	Output power	f=175MHz, VDD=7.2V	7	8	-	W
ηD1	Drain efficiency	Pin=0.3W, Idq=700mA	55	60	-	%
Pout2	Output power	f=520MHz, VDD=7.2V	7	8	-	W
ηD2	Drain efficiency	Pin=0.7W, Idq=750mA	50	55	-	%
	Load VSWR tolerance	VDD=9.2V, Po=7W(PinControl) f=175MHz, Idq=700mA, Zg=50Ω Load VSWR=20:1(All Phase)	No destroy			-
	Load VSWR tolerance	VDD=9.2V, Po=7W(PinControl) f=520MHz, Idq=750mA, Zg=50Ω Load VSWR=20:1(All Phase)	No destroy			-

Note : Above parameters , ratings , limits and conditions are subject to change.



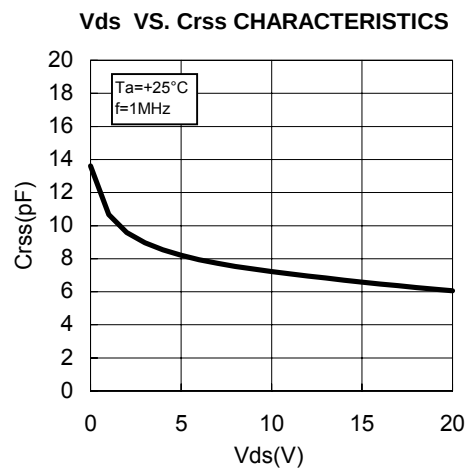
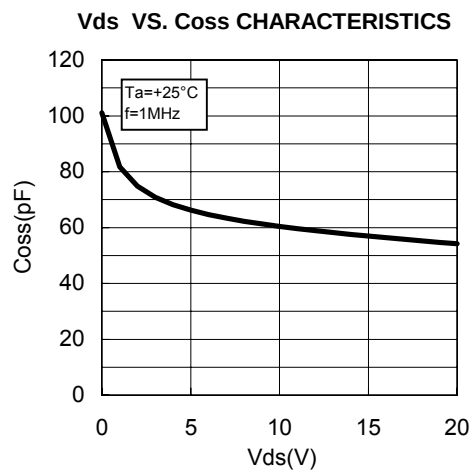
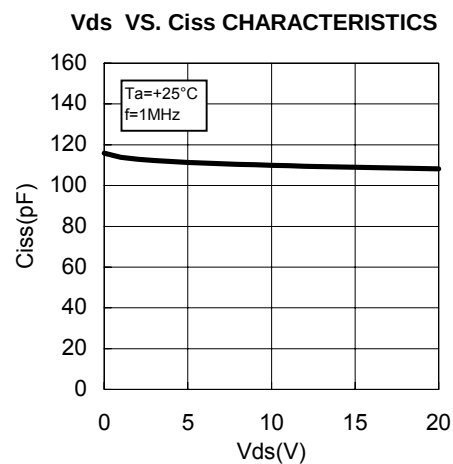
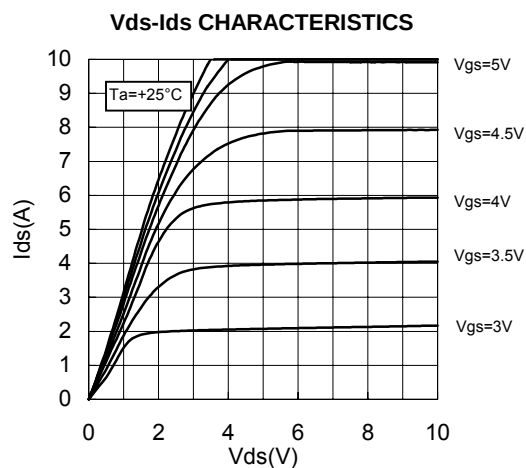
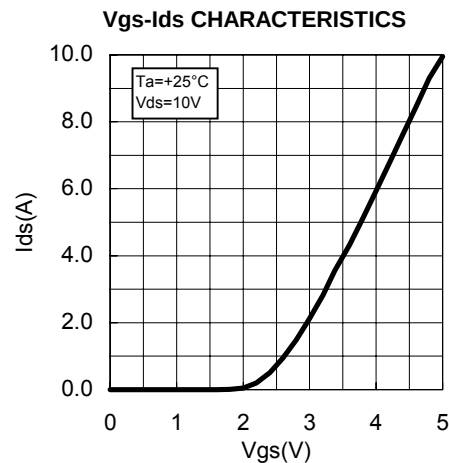
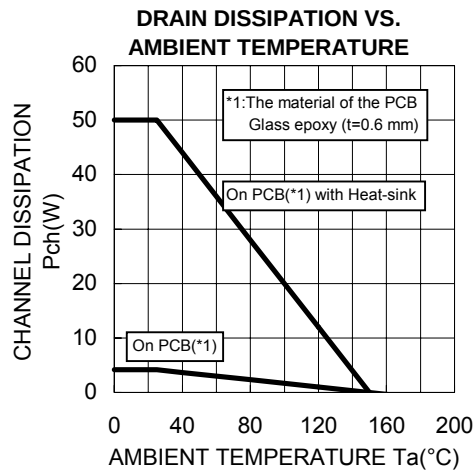
ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

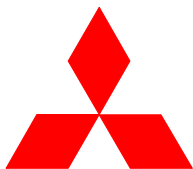
mitsubishi RF POWER MOS FET

RD07MVS1

Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

TYPICAL CHARACTERISTICS





ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

MITSUBISHI RF POWER MOS FET

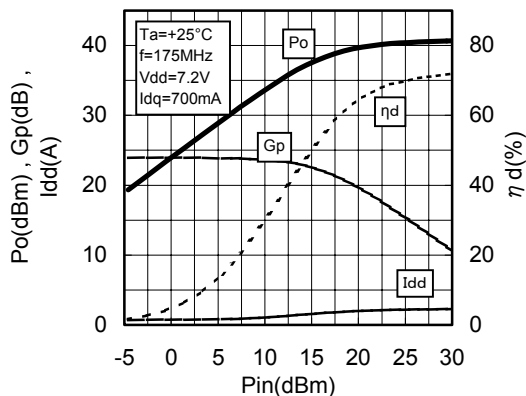
RD07MVS1

Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

TYPICAL CHARACTERISTICS

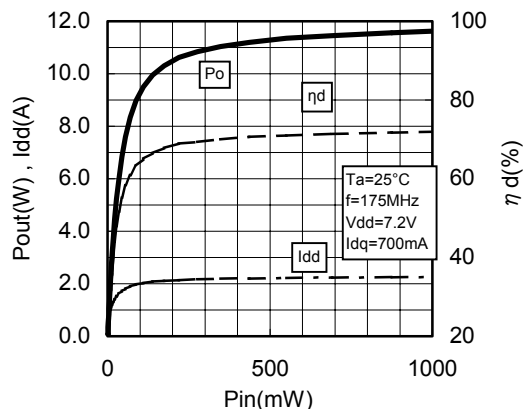
Pin-Po CHARACTERISTICS

@f=175MHz



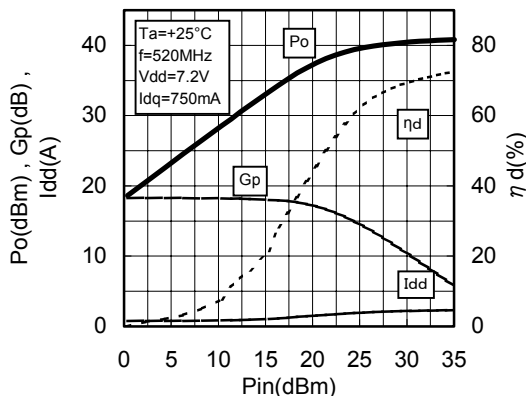
Pin-Po CHARACTERISTICS

@f=175MHz



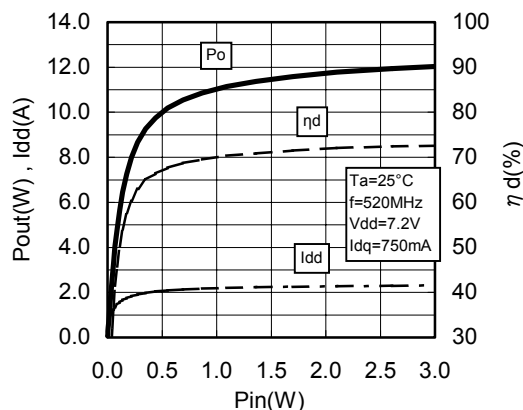
Pin-Po CHARACTERISTICS

@f=520MHz



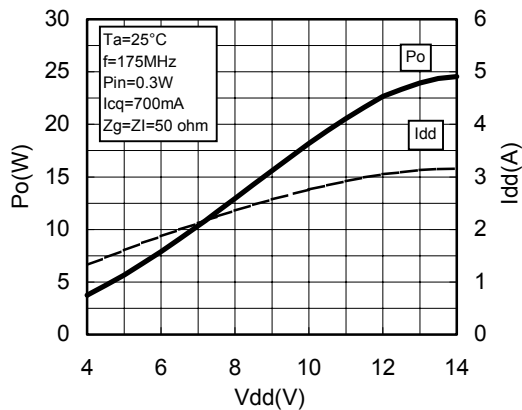
Pin-Po CHARACTERISTICS

@f=520MHz



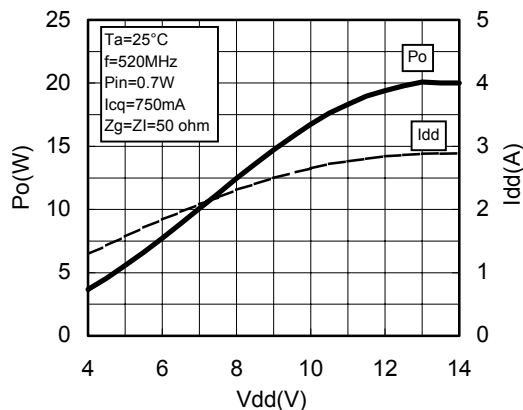
Vdd-Po CHARACTERISTICS

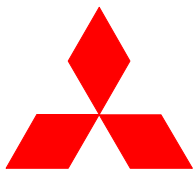
@f=175MHz



Vdd-Po CHARACTERISTICS

@f=520MHz





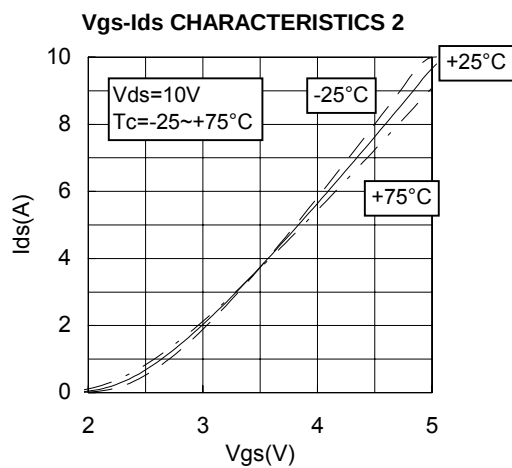
ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

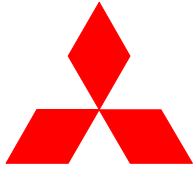
MITSUBISHI RF POWER MOS FET

RD07MVS1

Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

TYPICAL CHARACTERISTICS





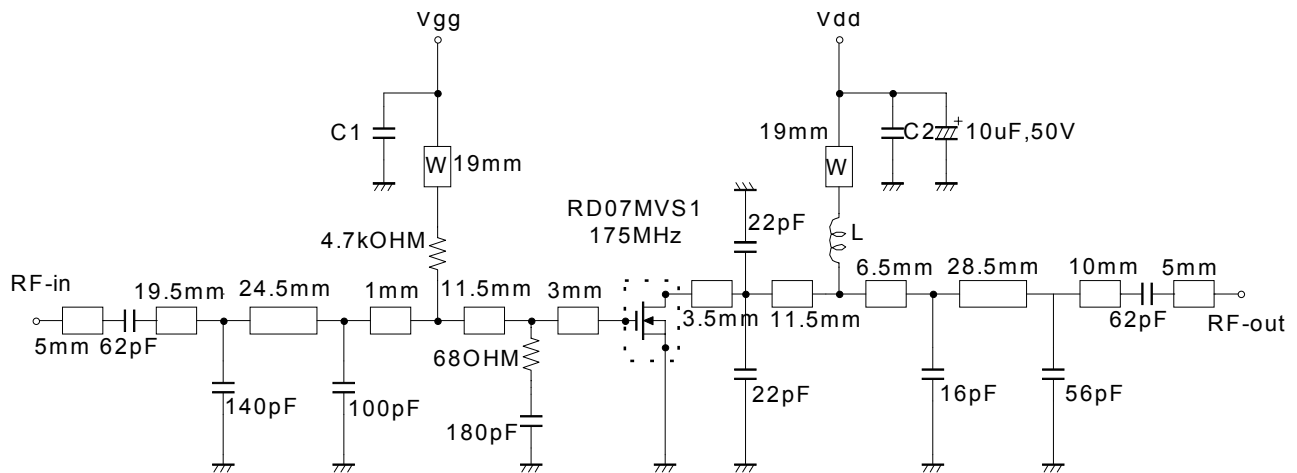
ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

MITSUBISHI RF POWER MOS FET

RD07MVS1

Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

TEST CIRCUIT(f=175MHz)



L: Enameled wire 7Turns, D:0.43mm, 2.46mm O.D

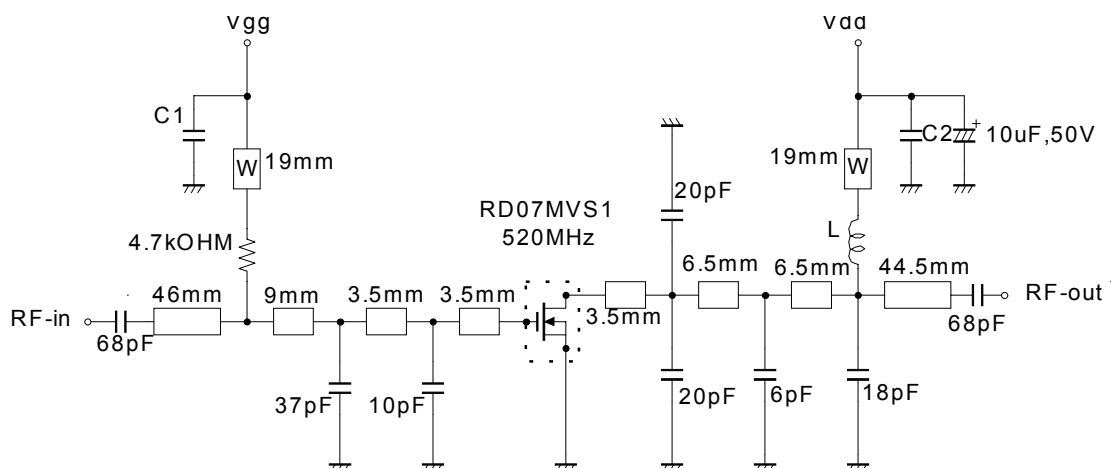
C1, C2: 1000pF, 0.022uF in parallel

Note: Board material- Teflon substrate

Micro strip line width=2.2mm/50OHM, er:2.7, t=0.8mm

W: line width=1.0mm

TEST CIRCUIT(f=520MHz)



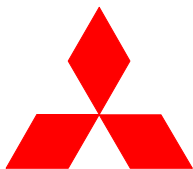
L: Enameled wire 5Turns, D:0.43mm, 2.46mm O.D

C1, C2: 1000pF, 0.022uF in parallel

Note: Board material- Teflon substrate

Micro strip line width=2.2mm/50OHM, er:2.7, t=0.8mm

W: line width=1.0mm



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

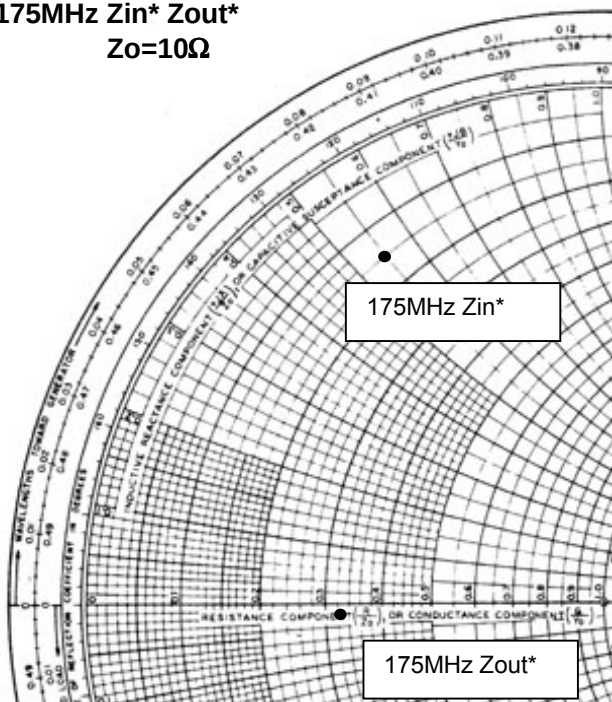
MITSUBISHI RF POWER MOS FET

RD07MVS1

Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

INPUT/OUTPUT IMPEDANCE VS. FREQUENCY CHARACTERISTICS

175MHz Z_{in}^* Z_{out}^*
 $Z_o=10\Omega$

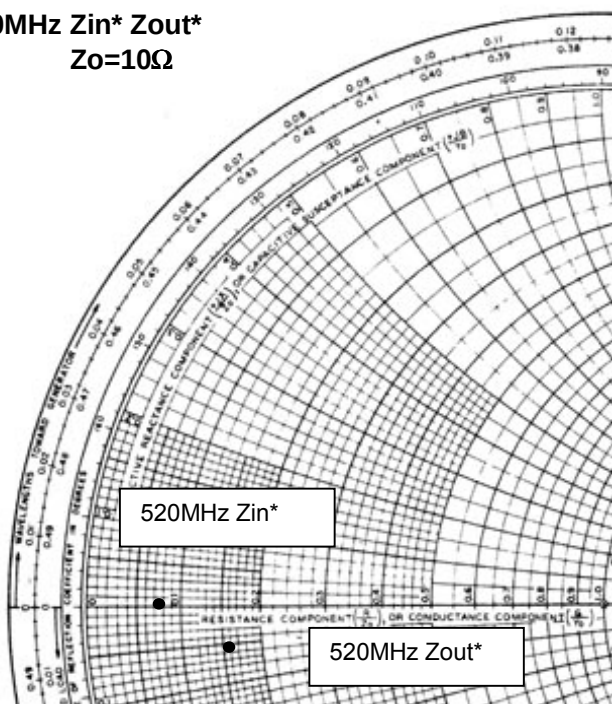


$V_{dd}=7.2V$, $I_{dq}=700mA$ (V_{gg} adj.), $P_{in}=0.28W$

$Z_{in}^*=1.55+j5.53$
 $Z_{out}^*=3.24-j0.26$

Z_{in}^* : Complex conjugate of input impedance
 Z_{out}^* : Complex conjugate of input impedance

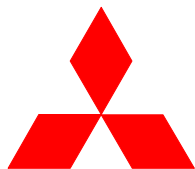
520MHz Z_{in}^* Z_{out}^*
 $Z_o=10\Omega$



$V_{dd}=7.2V$, $I_{dq}=750mA$ (V_{gg} adj.), $P_{in}=0.7W$

$Z_{in}^*=0.76+j0.06$
 $Z_{out}^*=1.61-j0.52$

Z_{in}^* : Complex conjugate of input impedance
 Z_{out}^* : Complex conjugate of input impedance



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

MITSUBISHI RF POWER MOS FET

RD07MVS1

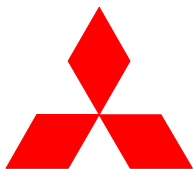
Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

RD07MVS1 S-PARAMETER DATA (@Vdd=7.2V, Id=750mA)

Freq. [MHz]	S11		S21		S12		S22	
	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)
100	0.890	-174.1	5.508	82.1	0.016	-3.6	0.790	-172.8
150	0.897	-175.6	3.613	75.0	0.015	-8.5	0.801	-174.0
175	0.899	-176.0	3.028	72.4	0.015	-9.6	0.802	-174.1
200	0.901	-176.3	2.604	70.1	0.014	-10.9	0.815	-174.0
250	0.907	-176.7	2.019	65.6	0.014	-12.7	0.844	-174.1
300	0.913	-177.0	1.614	60.7	0.012	-15.3	0.843	-174.1
350	0.918	-177.3	1.308	57.1	0.011	-15.8	0.860	-174.4
400	0.924	-177.8	1.102	54.1	0.010	-14.2	0.879	-175.0
450	0.928	-178.0	0.929	50.1	0.009	-14.8	0.882	-175.1
500	0.933	-178.3	0.790	48.6	0.008	-9.6	0.895	-175.5
520	0.935	-178.5	0.753	47.6	0.007	-7.7	0.901	-175.8
550	0.937	-178.8	0.692	45.3	0.007	-5.6	0.906	-176.2
600	0.940	-179.2	0.595	43.6	0.006	0.4	0.907	-176.6
650	0.942	-179.4	0.529	42.4	0.006	17.1	0.916	-177.2
700	0.944	-179.8	0.467	40.2	0.005	21.8	0.923	-177.6
750	0.947	-179.8	0.416	39.4	0.005	40.9	0.921	-178.0
800	0.948	-179.4	0.374	38.6	0.004	52.0	0.930	-178.8
850	0.949	-179.0	0.343	37.6	0.005	67.1	0.933	-178.9
900	0.951	-178.6	0.304	36.5	0.005	72.6	0.932	-179.3
950	0.951	-178.2	0.284	37.6	0.006	85.8	0.937	-179.8
1000	0.952	-177.9	0.262	35.1	0.007	85.1	0.938	-179.7
1050	0.950	-177.4	0.234	36.0	0.008	89.8	0.938	-179.3
1100	0.952	-176.9	0.226	35.8	0.009	93.4	0.940	-178.2

RD07MVS1 S-PARAMETER DATA (@Vdd=12.5V, Id=750mA)

Freq. [MHz]	S11		S21		S12		S22	
	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)
100	0.883	-172.1	6.013	81.0	0.017	-5.3	0.748	-170.4
150	0.891	-174.1	3.914	72.8	0.016	-10.7	0.765	-171.4
175	0.894	-174.6	3.269	69.8	0.016	-13.1	0.769	-171.4
200	0.897	-175.0	2.798	67.2	0.015	-14.9	0.786	-171.3
250	0.906	-175.6	2.144	62.1	0.014	-18.3	0.822	-171.4
300	0.914	-176.0	1.697	56.9	0.012	-20.4	0.828	-171.6
350	0.920	-176.4	1.361	53.0	0.011	-21.6	0.848	-172.0
400	0.927	-177.0	1.134	49.9	0.010	-21.2	0.871	-172.9
450	0.932	-177.4	0.949	45.8	0.009	-21.8	0.876	-173.2
500	0.937	-177.8	0.800	44.2	0.007	-16.9	0.892	-173.7
520	0.938	-178.0	0.761	43.2	0.007	-16.0	0.898	-174.1
550	0.940	-178.3	0.697	41.1	0.006	-13.3	0.904	-174.6
600	0.944	-178.8	0.594	39.3	0.005	-7.2	0.906	-175.1
650	0.946	-179.1	0.527	38.2	0.004	4.5	0.917	-175.9
700	0.948	-179.5	0.464	36.1	0.004	17.4	0.924	-176.3
750	0.950	-179.9	0.412	35.5	0.004	28.0	0.922	-176.9
800	0.951	-179.6	0.368	34.5	0.004	56.9	0.931	-177.8
850	0.953	-179.2	0.336	33.6	0.004	66.4	0.934	-178.0
900	0.954	-178.8	0.297	32.3	0.005	78.3	0.933	-178.3
950	0.954	-178.4	0.276	33.8	0.006	87.4	0.939	-179.4
1000	0.954	-178.0	0.254	31.1	0.006	90.9	0.941	-179.5
1050	0.952	-177.5	0.226	32.2	0.007	94.7	0.940	-179.9
1100	0.954	-177.0	0.219	32.0	0.008	98.0	0.943	-178.9



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

mitsubishi RF POWER MOS FET

RD07MVS1

Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W

—Keep safety first in your circuit designs! —

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

warning !

Do not use the device at the exceeded the maximum rating condition. In case of plastic molded devices, the exceeded maximum rating condition may cause blowout, smoldering or catch fire of the molding resin due to extreme short current flow between the drain and the source of the device. These results causes in fire or injury.